

TL08xx FET-Input Operational Amplifiers

1 Features

- High slew rate: 20V/μs (TL08xH, typ)
- Low offset voltage: 1mV (TL08xH, typ)
- Low offset voltage drift: 2 μV/°C
- Low power consumption: 940μA/ch (TL08xH, typ)
- Wide common-mode and differential voltage ranges
 - Common-mode input voltage range includes V_{CC+}
- Low input bias and offset currents
- Low noise: $V_n = 18\text{nV}/\sqrt{\text{Hz}}$ (typ) at $f = 1\text{kHz}$
- Output short-circuit protection
- Low total harmonic distortion: 0.003% (typ)
- Wide supply voltage: $\pm 2.25\text{V}$ to $\pm 20\text{V}$, 4.5V to 40V

2 Applications

- Solar energy: string and central inverter
- Motor drives: AC and servo drive control and power stage modules
- Single phase online UPS
- Three phase UPS
- Pro audio mixers
- Battery test equipment

3 Description

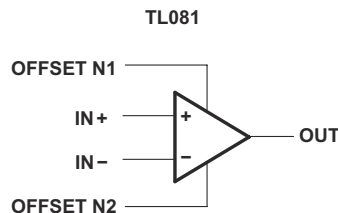
The TL08xH (TL081H, TL082H, and TL084H) family of devices are the next-generation versions of the industry-standard TL08x (TL081, TL082, and TL084) devices. These devices provide outstanding value for cost-sensitive applications, with features including low offset (1mV, typical), high slew rate (20V/μs), and common-mode input to the positive supply. High ESD (1.5kV, HBM), integrated EMI and RF filters, and operation across the full -40°C to 125°C enable the TL08xH devices to be used in the most rugged and demanding applications.

Device Information

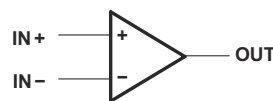
PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM) ⁽²⁾
TL081x	P (PDIP, 8)	9.59mm × 6.35mm
	DCK (SC70, 5)	2mm × 1.25mm
	PS (SO, 8)	6.2mm × 5.3mm
	D (SOIC, 8)	4.9mm × 3.9mm
	DBV (SOT-23, 5)	2.9mm × 1.6mm
TL082x	P (PDIP, 8)	9.59mm × 6.35mm
	PS (SO, 8)	6.2mm × 5.3mm
	D (SOIC, 8)	4.9mm × 3.9mm
	DDF (SOT-23, 8)	2.9mm × 1.6mm
	PW (TSSOP, 8)	4.4mm × 3mm
TL082M	JG (CDIP, 8)	9.6mm × 6.67mm
	FK (LCCC, 20)	8.89mm × 8.89mm
TL084x	N (PDIP, 14)	19.3mm × 6.35mm
	NS (SO, 14)	10.3mm × 5.3mm
	D (SOIC, 14)	8.65mm × 3.91mm
	DYY (SOT-23, 14)	4.2mm × 2mm
	PW (TSSOP, 14)	5mm × 4.4mm
TL084M	J (CDIP, 14)	19.56mm × 6.67mm
	FK (LCCC, 20)	8.89mm × 8.89mm

(1) For more information, see [Section 11](#).

(2) The body size (length × width) is a nominal value and does not include pins.



TL082 (EACH AMPLIFIER)
TL084 (EACH AMPLIFIER)



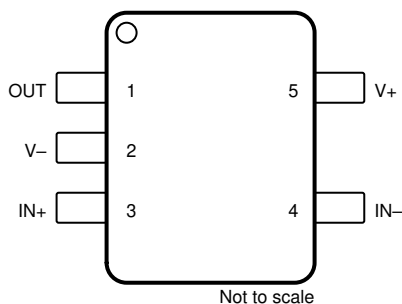
Logic Symbols



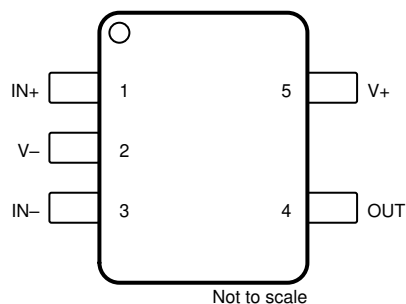
Table of Contents

1 Features	1	7.1 Overview.....	25
2 Applications	1	7.2 Functional Block Diagram.....	25
3 Description	1	7.3 Feature Description.....	25
4 Pin Configuration and Functions	3	7.4 Device Functional Modes.....	25
5 Specifications	9	8 Applications and Implementation	26
5.1 Absolute Maximum Ratings.....	9	8.1 Application Information.....	26
5.2 ESD Ratings.....	9	8.2 Typical Applications.....	26
5.3 Recommended Operating Conditions.....	9	8.3 System Examples.....	27
5.4 Thermal Information for Single Channel.....	10	8.4 Power Supply Recommendations.....	28
5.5 Thermal Information for Dual Channel.....	10	8.5 Layout.....	28
5.6 Thermal Information for Quad Channel.....	11	9 Device and Documentation Support	30
5.7 Electrical Characteristics: TL08xH.....	12	9.1 Receiving Notification of Documentation Updates....	30
5.8 Electrical Characteristics (DC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM.....	14	9.2 Support Resources.....	30
5.9 Electrical Characteristics (AC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM.....	16	9.3 Trademarks.....	30
5.10 Typical Characteristics: TL08xH.....	17	9.4 Electrostatic Discharge Caution.....	30
6 Parameter Measurement Information	24	9.5 Glossary.....	30
7 Detailed Description	25	10 Revision History	30
		11 Mechanical, Packaging, and Orderable Information	31

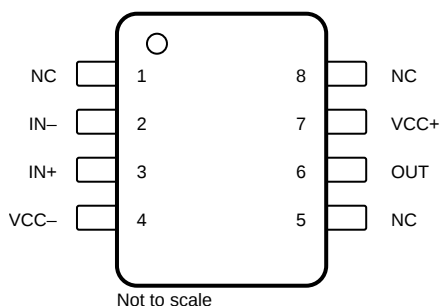
4 Pin Configuration and Functions



**Figure 4-1. TL081H DBV Package,
5-Pin SOT-23
(Top View)**



**Figure 4-2. TL081H DCK Package,
5-Pin SC70
(Top View)**



NC- no internal connection

**Figure 4-3. TL081H D Package,
8-Pin SOIC
(Top View)**

Table 4-1. Pin Functions: TL081H

PIN				TYPE ⁽¹⁾	DESCRIPTION
NAME	DBV	DCK	D		
IN–	4	3	2	I	Inverting input
IN+	3	1	3	I	Noninverting input
NC	—	—	8	—	Do not connect
NC	—	—	1	—	Do not connect
NC	—	—	5	—	Do not connect
OUT	1	4	6	O	Output
VCC–	2	2	4	—	Power supply
VCC+	5	5	7	—	Power supply

(1) I = input, O = output



NC- no internal connection

**Figure 4-4. TL081x D, P, and PS Package,
8-Pin SOIC, PDIP, and SO
(Top View)**

Table 4-2. Pin Functions: TL081x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
IN–	2	I	Inverting input
IN+	3	I	Noninverting input
NC	8	—	Do not connect
OFFSET N1	1	—	Input offset adjustment
OFFSET N2	5	—	Input offset adjustment
OUT	6	O	Output
VCC–	4	—	Power supply
VCC+	7	—	Power supply

(1) I = input, O = output

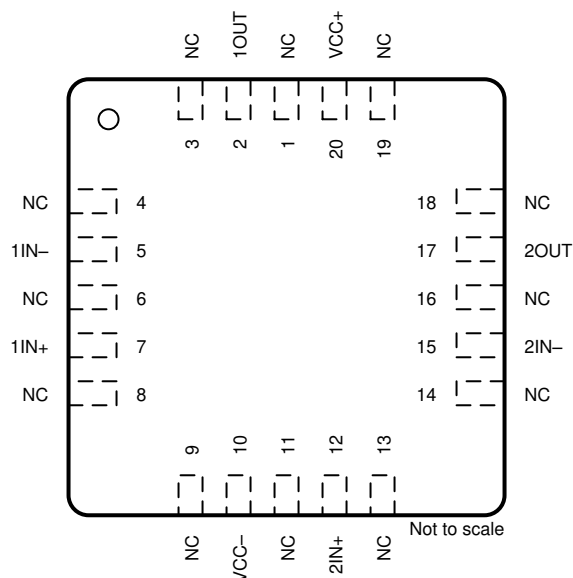


**Figure 4-5. TL082x D, DDF, DGK, JG, P, PS, and PW Package,
8-Pin SOIC, SOT-23 (8), VSSOP, CDIP, PDIP, SO, and TSSOP
(Top View)**

Table 4-3. Pin Functions: TL082x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1IN–	2	I	Inverting input
1IN+	3	I	Noninverting input
1OUT	1	O	Output
2IN–	6	I	Inverting input
2IN+	5	I	Noninverting input
2OUT	7	O	Output
VCC–	4	—	Power supply
VCC+	8	—	Power supply

(1) I = input, O = output



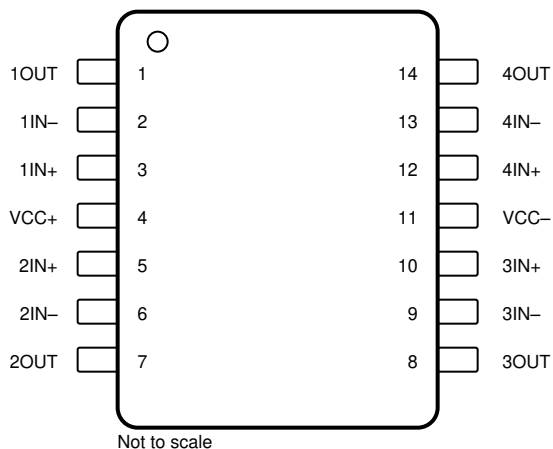
NC- no internal connection

**Figure 4-6. TL082 FK Package,
20-Pin LCCC
(Top View)**

Table 4-4. Pin Functions: TL082x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1IN–	5	I	Inverting input
1IN+	7	I	Noninverting input
1OUT	2	O	Output
2IN–	15	I	Inverting input
2IN+	12	I	Noninverting input
2OUT	17	O	Output
NC	1, 3, 4, 6, 8, 9, 11, 13, 14, 16, 18, 19	—	Do not connect
VCC–	10	—	Power supply
VCC+	20	—	Power supply

(1) I = input, O = output

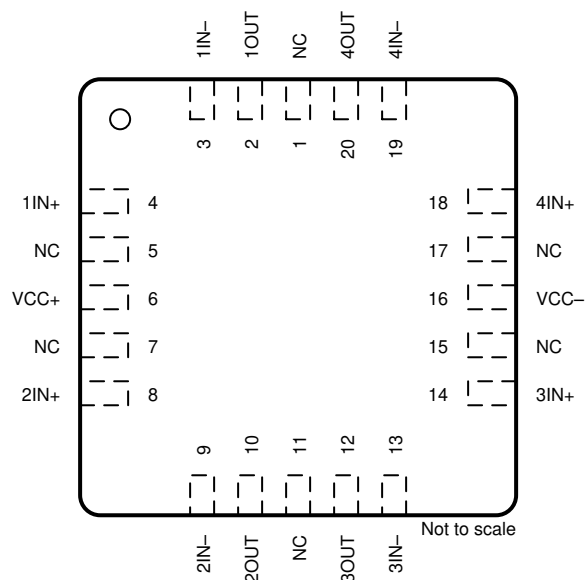


**Figure 4-7. TL084x D, N, NS, PW, J, and DYY Package,
14-Pin SOIC, PDIP, SO, TSSOP, CDIP, and SOT-23 (14)
(Top View)**

Table 4-5. Pin Functions: TL084x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1IN–	2	I	Inverting input
1IN+	3	I	Noninverting input
1OUT	1	O	Output
2IN–	6	I	Inverting input
2IN+	5	I	Noninverting input
2OUT	7	O	Output
3IN–	9	I	Inverting input
3IN+	10	I	Noninverting input
3OUT	8	O	Output
4IN–	13	I	Inverting input
4IN+	12	I	Noninverting input
4OUT	14	O	Output
V _{CC} –	11	—	Power supply
V _{CC} +	4	—	Power supply

(1) I = input, O = output



NC- no internal connection

**Figure 4-8. TL084 FK Package,
20-Pin LCCC
(Top View)**

Table 4-6. Pin Functions: TL084x

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1IN–	3	I	Inverting input
1IN+	4	I	Noninverting input
1OUT	2	O	Output
2IN–	9	I	Inverting input
2IN+	8	I	Noninverting input
2OUT	10	O	Output
3IN–	13	I	Inverting input
3IN+	14	I	Noninverting input
3OUT	12	O	Output
4IN–	19	I	Inverting input
4IN+	18	I	Noninverting input
4OUT	20	O	Output
NC	1, 5, 7, 11, 15, 17	—	Do not connect
VCC–	16	—	Power supply
VCC+	6	—	Power supply

(1) I = input, O = output

5 Specifications

5.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT
Supply voltage, $V_S = (V+) - (V-)$		All NS and PS packages; All TL08xM devices	-0.3	36	V
		All other devices	0	42	V
Signal input pins	Common-mode voltage ⁽³⁾	All NS and PS packages; All TL08xM devices	(V-) - 0.3	(V-) + 36	V
		All other devices	(V-) - 0.5	(V+) + 0.5	V
	Differential voltage ⁽³⁾	All NS and PS packages; All TL08xM devices ⁽⁴⁾	(V-) - 0.3	(V-) + 36	V
		All other devices		$V_S + 0.2$	V
	Current ⁽³⁾	All NS and PS packages; All TL07xM devices		50	mA
		All other devices	-10	10	mA
Output short-circuit ⁽²⁾			Continuous		
Operating ambient temperature, T_A			-55	150	°C
Junction temperature, T_J				150	°C
Case temperature for 60 seconds - FK package				260	°C
Lead temperature 1.8 mm (1/16 inch) from case for 10 seconds				300	°C
Storage temperature, T_{sto}			-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Short-circuit to ground, one amplifier per package.
- (3) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5V beyond the supply rails must be current limited to 10 mA or less.
- (4) Differential voltage only limited by input voltage.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_S	Supply voltage, $(V+) - (V-)$	All NS and PS packages; All TL08xM devices ⁽¹⁾	10	30	V
		All other devices	4.5	40	V
V_I	Input voltage range	All NS and PS packages; All TL08xM devices	$(V-) + 2$	$(V+) + 0.1$	V
		All other devices	$(V-) + 4$	$(V+) + 0.1$	V
T_A	Specified temperature	TL08xM	-55	125	°C
		TL08xH	-40	125	°C
		TL08xL	-40	85	°C
		TL08xC	0	70	°C

- (1) $V+$ and $V-$ are not required to be of equal magnitude, provided that the total V_S ($V+ - V-$) is between 10V and 30V.

5.4 Thermal Information for Single Channel

THERMAL METRIC ⁽¹⁾		TL081xx					UNIT
		D (SOIC)	DCK (SC70)	DBV (SOT-23)	P (PDIP)	PS (SO)	
		8 PINS	5 PINS	5 PINS	8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	158.8	217.5	212.2	85	95	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	98.6	113.1	111.1	–	–	°C/W
R _{θJB}	Junction-to-board thermal resistance	102.3	63.8	79.4	–	–	°C/W
ψ _{JT}	Junction-to-top characterization parameter	45.8	34.8	51.8	–	–	°C/W
ψ _{JB}	Junction-to-board characterization parameter	101.5	63.5	79.0	–	–	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.5 Thermal Information for Dual Channel

THERMAL METRIC ⁽¹⁾		TL082xx								UNIT
		D (SOIC)	DDF (SOT-23)	FK (LCCC)	JG (CDIP)	P (PDIP)	PS (SO)	PW (TSSOP)	U (CFP)	
		8 PINS	8 PINS	20 PINS	8 PINS	8 PINS	8 PINS	8 PINS	10 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	147.8	181.5	–	–	85	95	200.3	169.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	88.2	112.5	5.61	15.05	–	–	89.4	62.1	°C/W
R _{θJB}	Junction-to-board thermal resistance	91.4	98.2	–	–	–	–	131.0	176.2	°C/W
ψ _{JT}	Junction-to-top characterization parameter	36.8	17.2	–	–	–	–	22.2	48.4	°C/W
ψ _{JB}	Junction-to-board characterization parameter	90.6	97.6	–	–	–	–	129.3	144.1	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	–	–	–	–	N/A	5.4	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.6 Thermal Information for Quad Channel

THERMAL METRIC ⁽¹⁾		TL084xx								UNIT
		D (SOIC)	DYY (SOT-23)	FK (TSSOP)	J (TSSOP)	N (TSSOP)	NS (TSSOP)	PW (TSSOP)	W (TSSOP)	
		14 PINS	14 PINS	20 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	114.2	153.2	–	–	80	76	–	128.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	70.3	88.7	5.61	14.5	–	–	14.5	56.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	70.2	65.4	–	–	–	–	–	127.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	28.8	9.5	–	–	–	–	–	29	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	69.8	65.0	–	–	–	–	–	106.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	–	–	–	–	–	0.5	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.7 Electrical Characteristics: TL08xH

For $V_S = (V_{CC+}) - (V_{CC-}) = 4.5V$ to $40V$ ($\pm 2.25V$ to $\pm 20V$) at $T_A = 25^\circ C$, $R_L = 10k\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V _{OS}	Input offset voltage				±1	±4	mV
			T _A = −40°C to 125°C			±5	
dV _{OS} /dT	Input offset voltage drift		T _A = −40°C to 125°C		±2		μV/°C
PSRR	Input offset voltage versus power supply	V _S = 5V to 40V, V _{CM} = V _S / 2	T _A = −40°C to 125°C		±1	±10	μV/V
	Channel separation	f = 0Hz			10		μV/V
INPUT BIAS CURRENT							
I _B	Input bias current				±1	±120	pA
			DCK and DBV packages		±1	±300	pA
			T _A = −40°C to 125°C ⁽¹⁾			±5	nA
I _{OS}	Input offset current				±0.5	±120	pA
			DCK and DBV packages		±0.5	±250	pA
			T _A = −40°C to 125°C ⁽¹⁾			±5	nA
NOISE							
E _N	Input voltage noise	f = 0.1Hz to 10Hz			9.2		μV _{PP}
					1.4		μV _{RMS}
e _N	Input voltage noise density	f = 1kHz			37		nV/√Hz
		f = 10kHz			21		
i _N	Input current noise	f = 1kHz			80		fA/√Hz
INPUT VOLTAGE RANGE							
V _{CM}	Common-mode voltage range			(V _{CC−}) + 1.5		(V _{CC+})	V
CMRR	Common-mode rejection ratio	V _S = 40V, (V _{CC−}) + 2.5V < V _{CM} < (V _{CC+}) − 1.5V		100	105		dB
			T _A = −40°C to 125°C	95			dB
		V _S = 40V, (V _{CC−}) + 2.5V < V _{CM} < (V _{CC+})		90	105		dB
			T _A = −40°C to 125°C	80			dB
INPUT CAPACITANCE							
Z _{ID}	Differential				100 2		MΩ pF
Z _{ICM}	Common-mode				6 1		TΩ pF
OPEN-LOOP GAIN							
A _{OL}	Open-loop voltage gain	V _S = 40V, V _{CM} = V _S / 2, (V _{CC−}) + 0.3V < V _O < (V _{CC+}) − 0.3V	T _A = −40°C to 125°C	118	125		dB
A _{OL}	Open-loop voltage gain	V _S = 40V, V _{CM} = V _S / 2, R _L = 2kΩ, (V _{CC−}) + 1.2V < V _O < (V _{CC+}) − 1.2V	T _A = −40°C to 125°C	115	120		dB
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product				5.25		MHz
SR	Slew rate	V _S = 40V, G = +1, C _L = 20pF			20		V/μs
t _S	Settling time	To 0.1%, V _S = 40V, V _{STEP} = 10V , G = +1, CL = 20pF			0.63		μs
		To 0.1%, V _S = 40V, V _{STEP} = 2V , G = +1, CL = 20pF			0.56		
		To 0.01%, V _S = 40V, V _{STEP} = 10V , G = +1, CL = 20pF			0.91		
		To 0.01%, V _S = 40V, V _{STEP} = 2V , G = +1, CL = 20pF			0.48		
	Phase margin	G = +1, R _L = 10kΩ, C _L = 20pF			56		°
	Overload recovery time	V _{IN} × gain > V _S			300		ns
THD+N	Total harmonic distortion + noise	V _S = 40V, V _O = 6V _{RMS} , G = +1, f = 1kHz			0.00012		%
EMIRR	EMI rejection ratio	f = 1GHz			53		dB
OUTPUT							

5.7 Electrical Characteristics: TL08xH (continued)

For $V_S = (V_{CC+}) - (V_{CC-}) = 4.5V$ to $40V$ ($\pm 2.25V$ to $\pm 20V$) at $T_A = 25^\circ C$, $R_L = 10k\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{O\ UT} = V_S / 2$, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
	Voltage output swing from rail	Positive rail headroom	$V_S = 40V, R_L = 10k\Omega$		115	210	mV
			$V_S = 40V, R_L = 2k\Omega$		520	965	
		Negative rail headroom	$V_S = 40V, R_L = 10k\Omega$		105	215	
			$V_S = 40V, R_L = 2k\Omega$		500	1030	
I_{SC}	Short-circuit current				±26		mA
C_{LOAD}	Capacitive load drive				300		pF
Z_O	Open-loop output impedance	$f = 1MHz, I_O = 0\ A$			125		Ω
POWER SUPPLY							
I_Q	Quiescent current per amplifier	$I_O = 0\ A$	$T_A = -40^{\circ}C\ to\ 125^{\circ}C$		937.5	1125	μA
		$I_O = 0\ A, (TL081H)$			960	1156	
		$I_O = 0\ A$				1130	
		$I_O = 0\ A, (TL082H)$				1143	
		$I_O = 0\ A, (TL071H)$				1160	
	Turn-On Time	At $T_A = 25^{\circ}C, V_S = 40V, V_S$ ramp rate $> 0.3V/\mu s$			60		μs

(1) Max I_B and I_{OS} data is specified based on characterization results.

5.8 Electrical Characteristics (DC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM

For $V_S = (V_{CC+}) - (V_{CC-}) = \pm 15V$ at $T_A = 25^\circ C$, unless otherwise noted

PARAMETER		TEST CONDITIONS ^{(1) (2)}			MIN	TYP	MAX	UNIT
V _{OS}	Input offset voltage	V _O = 0V R _S = 50 Ω	TL08xC		3	10	mV	
				T _A = Full range	13			
			TL08xAC		3	6		
				T _A = Full range	7.5			
			TL08xBC		2	3		
				T _A = Full range	5			
			TL08xI		3	6		
				T _A = Full range	8			
			TL081M, TL082M		3	6		
				T _A = Full range	9			
TL084M		3	9					
	T _A = Full range	15						
dV _{OS} /dT	Input offset voltage drift	V _O = 0V, R _S = 50 Ω	T _A = Full range		±18			μV/°C
I _{OS}	Input offset current	V _O = 0V	TL08xC		5	100	pA	
				T _A = Full range	10	nA		
			TL08xAC, TL08xBC, TL08xI		5	100	pA	
				T _A = Full range	2	nA		
			TL08xM		5	100	pA	
				T _A = Full range	20	nA		
I _B	Input bias current	V _O = 0V	TL08xC, TL08xAC, TL08xBC, TL08xI		65	200	pA	
				T _A = Full range	7	nA		
			TL081M, TL082M		65	200	pA	
				T _A = Full range	50	nA		
			TL084M		65	200	pA	
				T _A = Full range	20	nA		
V _{CM}	Common-mode voltage range				±11	–12 to 15		V
V _{OM}	Maximum peak output voltage swing	R _L = 10kΩ			±12	±13.5	V	
		R _L ≥ 10kΩ	T _A = Full range		±12			
		R _L ≥ 2kΩ			±10			
A _{OL}	Open-loop voltage gain	V _O = 0V	TL08xC		25	200	V/mV	
				T _A = Full range	15			
			TL08xAC, TL08xBC, TL08xI		50	200		
				T _A = Full range	25			
			TL08xM		35	200		
				T _A = Full range	15			
GBW	Gain-bandwidth product	All NS and PS packages; All TL08xM devices			3	MHz		
		All other devices			5.25			
R _{ID}	Common-mode input resistance				1	TΩ		
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICR(min)} V _O = 0V R _S = 50 Ω	TL08xC		70	100	dB	
			TL08xAC, TL08xBC, TL08xI		75	100		
			TL08xM		80	86		
PSRR	Input offset voltage versus power supply	V _S = ±9V to ± 18V V _O = 0V R _S = 50 Ω	TL08xC		70	100	dB	
			TL08xAC, TL08xBC, TL08xI		80	100		
			TL08xM		80	86		

5.8 Electrical Characteristics (DC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM (continued)

For $V_S = (V_{CC+}) - (V_{CC-}) = \pm 15V$ at $T_A = 25^\circ C$, unless otherwise noted

PARAMETER		TEST CONDITIONS ^{(1) (2)}	MIN	TYP	MAX	UNIT
I_Q	Quiescent current per amplifier	$V_O = 0V$; no load		1.4	2.5	mA
	Channel separation	$f = 0Hz$		1		$\mu V/V$

(1) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified.

(2) Full range is $T_A = 0^\circ C$ to $70^\circ C$ for the TL07xC, TL07xAC, and TL07xBC; $T_A = -40^\circ C$ to $85^\circ C$ for the TL07xI; and $T_A = -55^\circ C$ to $125^\circ C$ for the TL07xM.

5.9 Electrical Characteristics (AC): TL08xC, TL08xAC, TL08xBC, TL08xI, TL08xM

For $V_S = (V_{CC+}) - (V_{CC-}) = \pm 15V$ at $T_A = 25^\circ C$, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
SR	Slew rate	$V_I = 10V$, $C_L = 100pF$, $R_L = 2k\Omega$	TL08xM	5	20		V/ μs
			TL08xC, TL08xAC, TL08xBC, TL08xI	8	20		V/ μs
t_s	Settling time	$V_I = 20V$, $C_L = 100pF$, $R_L = 2k\Omega$			0.1		μs
					20%		
e_N	Input voltage noise density	All PS and NS packages; All TL08xM devices	$R_S = 20\Omega$, $f = 1kHz$		18		$nV/\sqrt{Hz}$
		All other devices	$f = 1kHz$		37		$nV/\sqrt{Hz}$
			$f = 10kHz$		21		
E_N	Input voltage noise	All PS and NS packages; All TL08xM devices	$R_S = 20\Omega$, $f = 10Hz$ to $10kHz$		4		μV_{RMS}
		All other devices	$f = 0.1Hz$ to $10Hz$		1.4		μV_{RMS}
i_N	Input current noise	$R_S = 20\Omega$, $f = 1kHz$			10		$fA/\sqrt{Hz}$
	Phase margin	TL08xC, TL08xAC, TL08xBC, TL08xI	$G = +1$, $R_L = 10k\Omega$, $C_L = 20pF$		56		°
	Overload recovery time	$V_{IN} \times \text{gain} > V_S$			300		ns
THD+N	Total harmonic distortion + noise	All PS and NS packages; All TL08xM devices	$V_O = 6V_{RMS}$, $R_L \geq 2k\Omega$, $f = 1kHz$, $G = +1$, $R_S \leq 1k\Omega$		0.003		%
		All other devices	$V_S = 40V$, $V_O = 6V_{RMS}$, $G = +1$, $f = 1kHz$		0.00012		%
EMIRR	EMI rejection ratio	TL08xC, TL08xAC, TL08xBC, TL08xI	$f = 1GHz$		53		dB
Z_O	Open-loop output impedance	TL07xC, TL07xAC, TL07xBC, TL07xI	$f = 1MHz$, $I_O = 0A$		125		Ω

5.10 Typical Characteristics: TL08xH

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

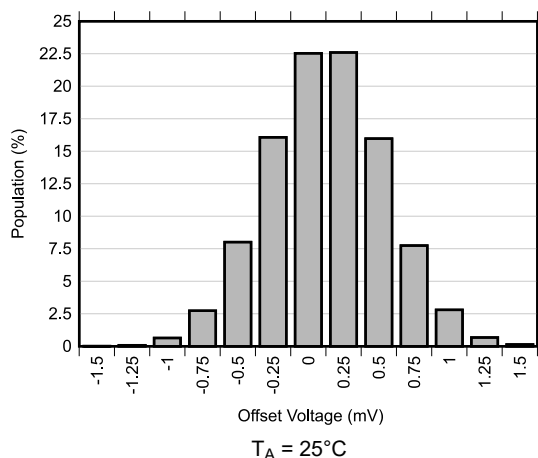


Figure 5-1. Offset Voltage Production Distribution

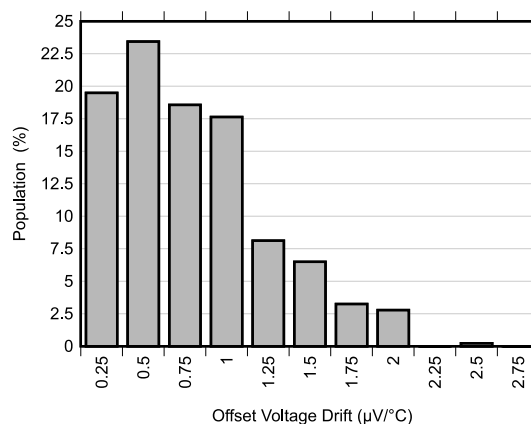


Figure 5-2. Offset Voltage Drift Distribution

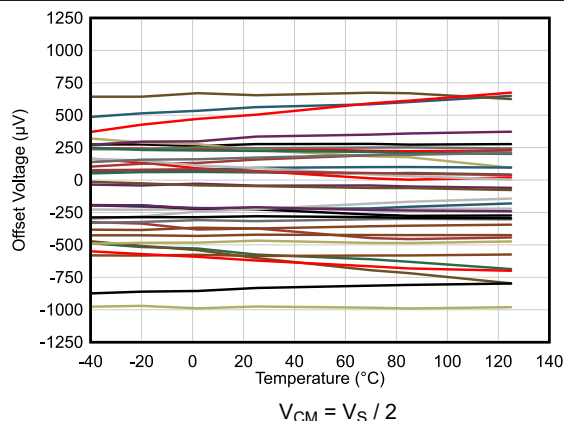


Figure 5-3. Offset Voltage vs Temperature

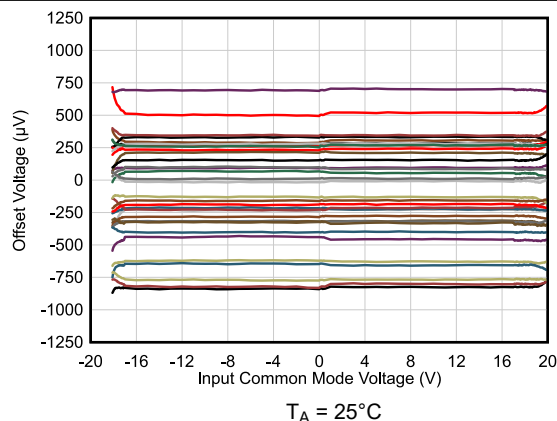


Figure 5-4. Offset Voltage vs Common-Mode Voltage

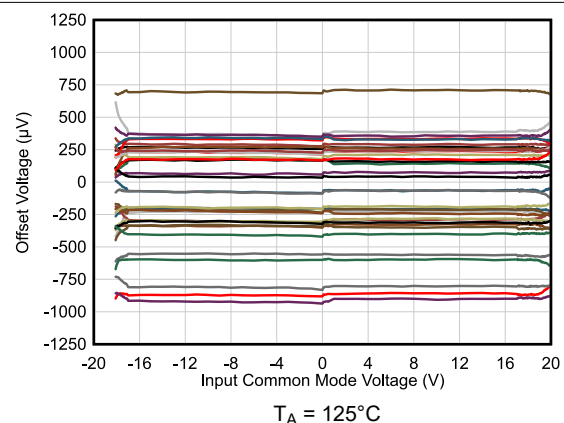


Figure 5-5. Offset Voltage vs Common-Mode Voltage

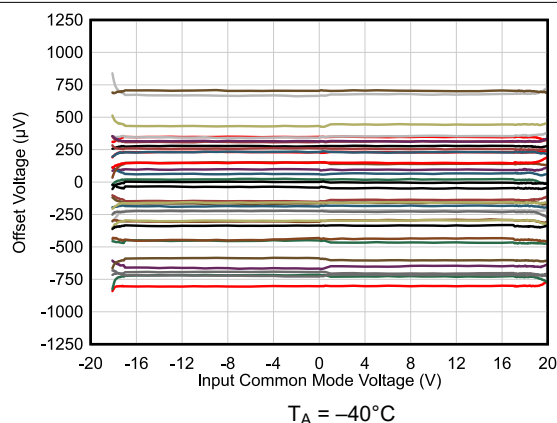


Figure 5-6. Offset Voltage vs Common-Mode Voltage

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

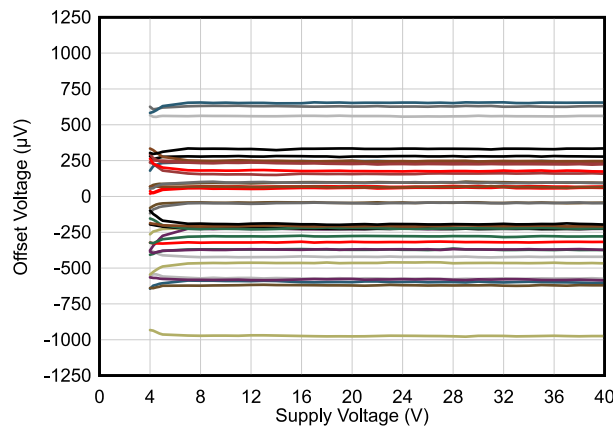


Figure 5-7. Offset Voltage vs Power Supply

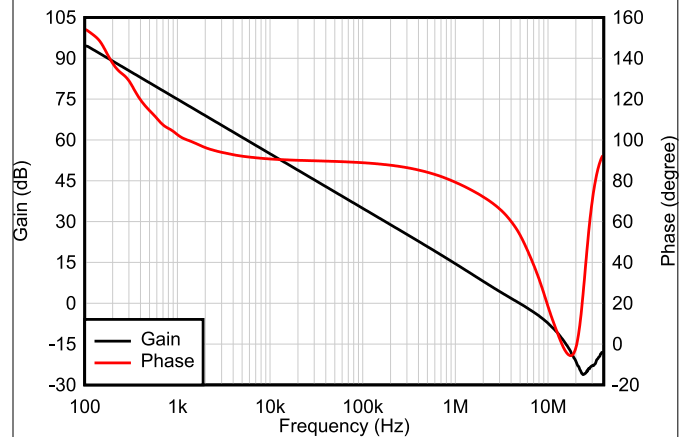


Figure 5-8. Open-Loop Gain and Phase vs Frequency

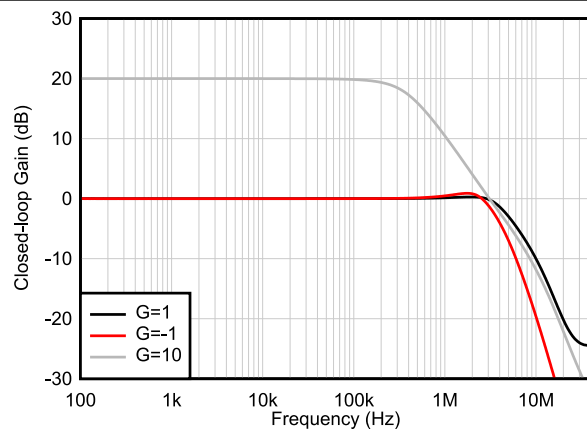


Figure 5-9. Closed-Loop Gain vs Frequency

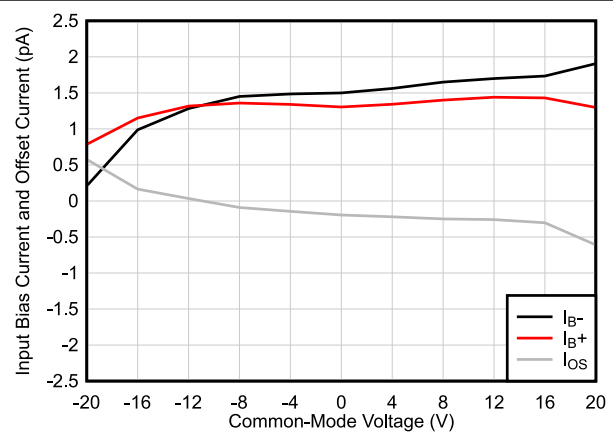


Figure 5-10. Input Bias Current vs Common-Mode Voltage

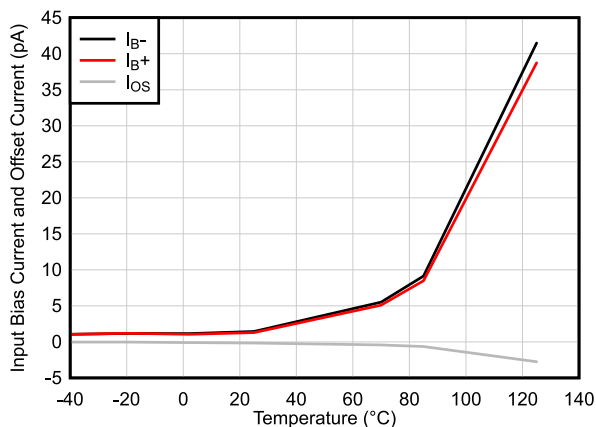


Figure 5-11. Input Bias Current vs Temperature

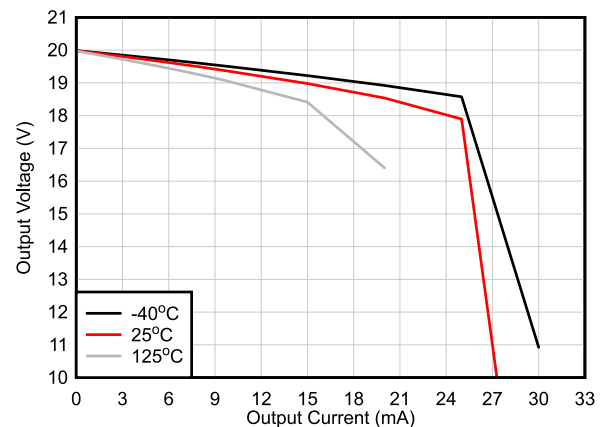


Figure 5-12. Output Voltage Swing vs Output Current (Sourcing)

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

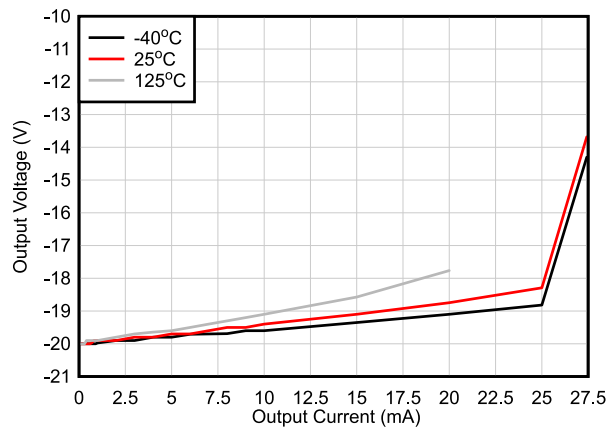


Figure 5-13. Output Voltage Swing vs Output Current (Sinking)

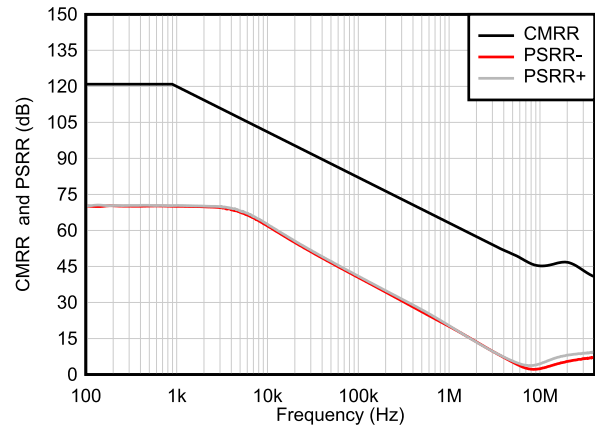


Figure 5-14. CMRR and PSRR vs Frequency

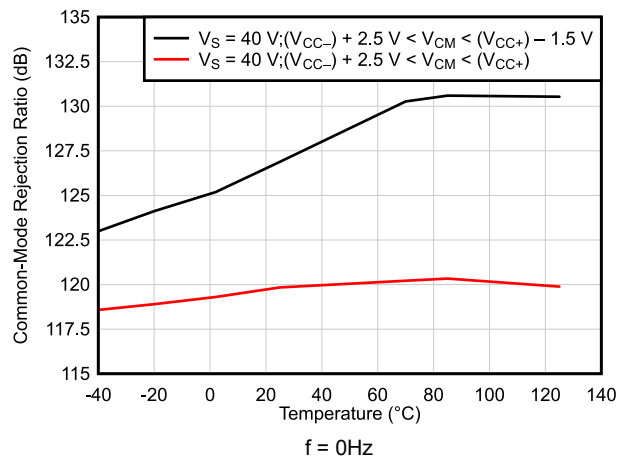


Figure 5-15. CMRR vs Temperature (dB)

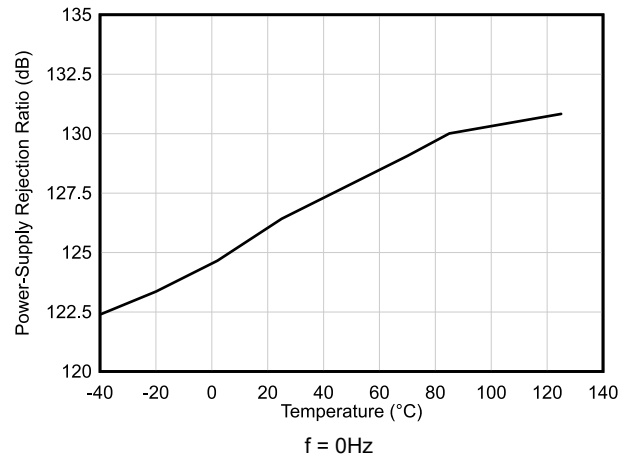


Figure 5-16. PSRR vs Temperature (dB)

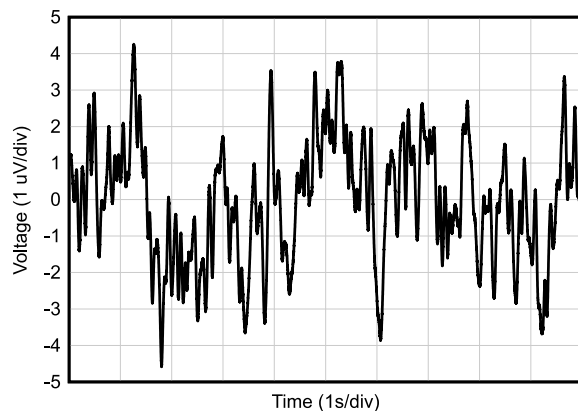


Figure 5-17. 0.1-Hz to 10-Hz Noise

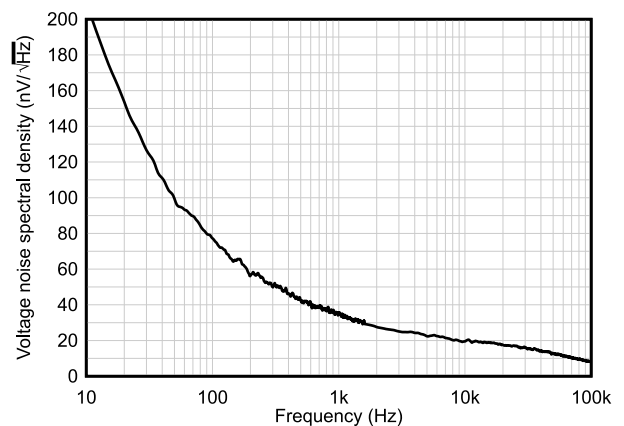


Figure 5-18. Input Voltage Noise Spectral Density vs Frequency

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

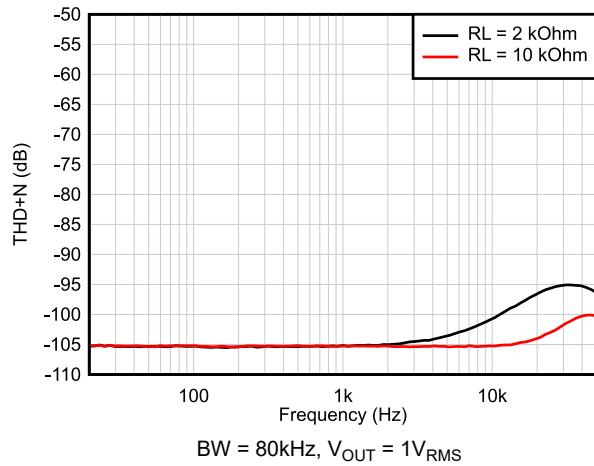


Figure 5-19. THD+N Ratio vs Frequency

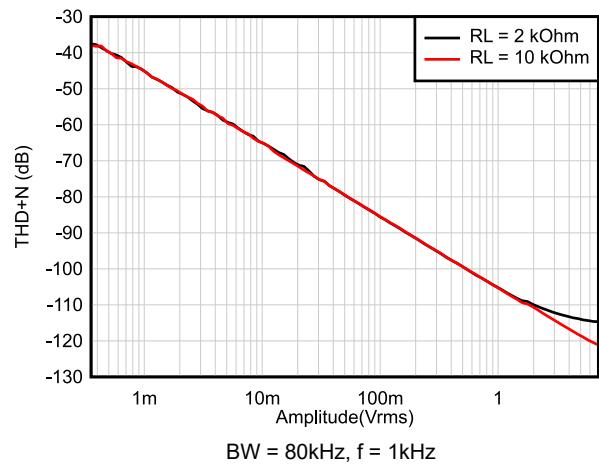


Figure 5-20. THD+N vs Output Amplitude

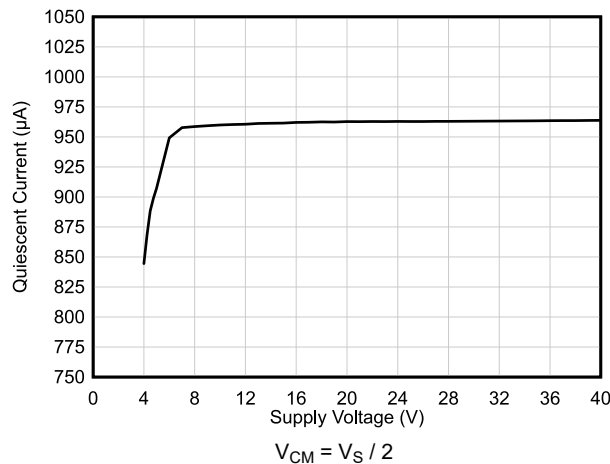


Figure 5-21. Quiescent Current vs Supply Voltage

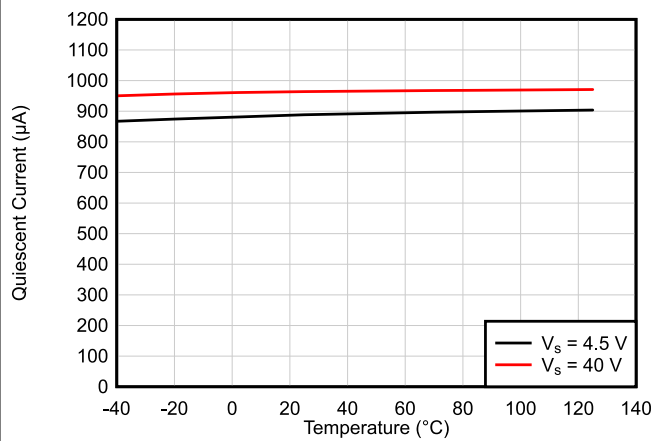


Figure 5-22. Quiescent Current vs Temperature

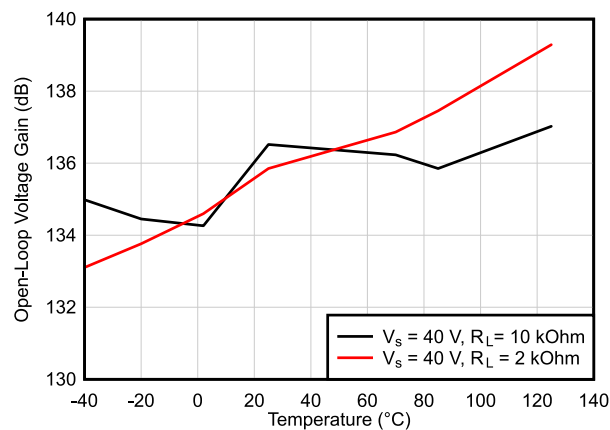


Figure 5-23. Open-Loop Voltage Gain vs Temperature (dB)

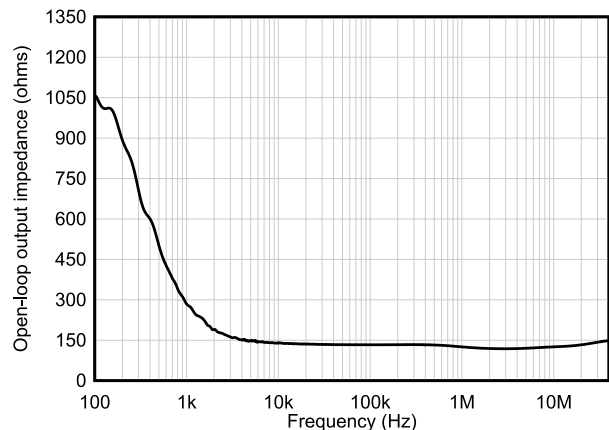


Figure 5-24. Open-Loop Output Impedance vs Frequency

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

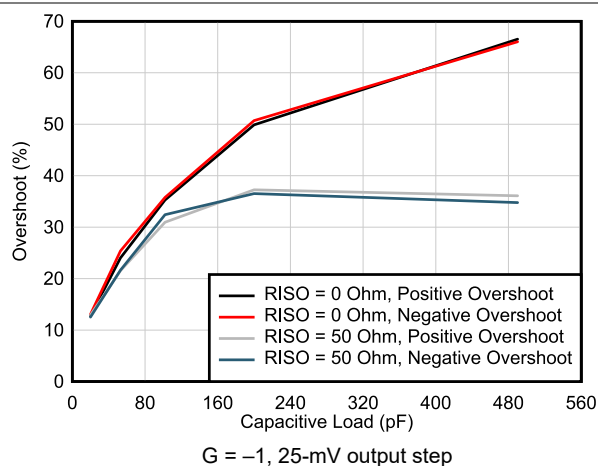


Figure 5-25. Small-Signal Overshoot vs Capacitive Load

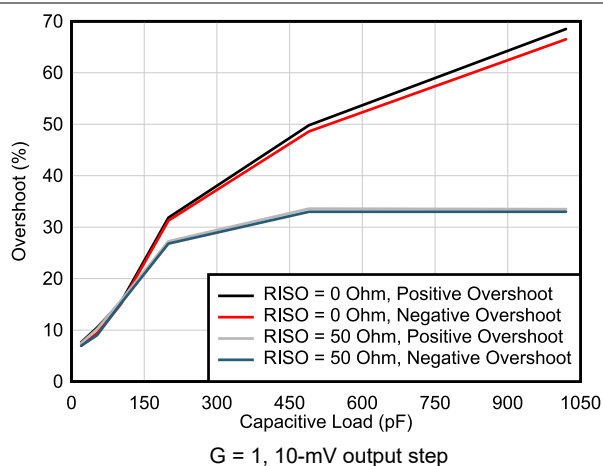


Figure 5-26. Small-Signal Overshoot vs Capacitive Load

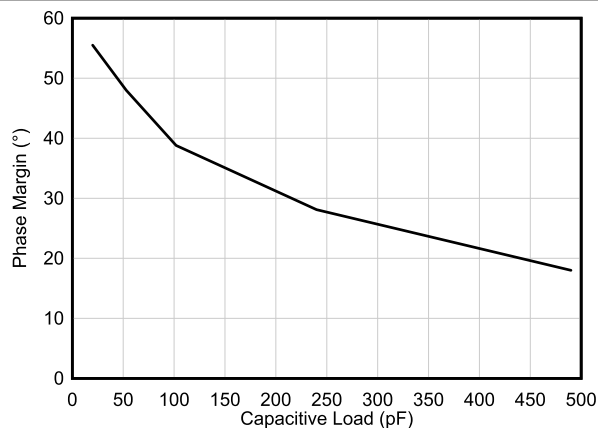


Figure 5-27. Phase Margin vs Capacitive Load

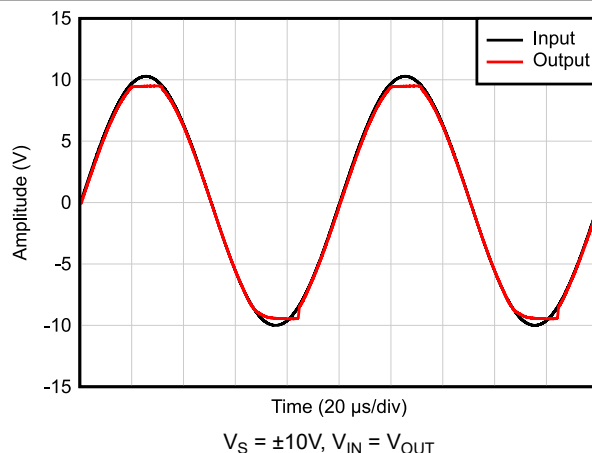


Figure 5-28. No Phase Reversal

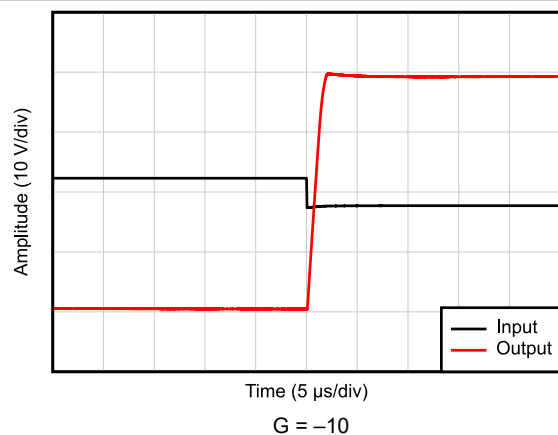


Figure 5-29. Positive Overload Recovery

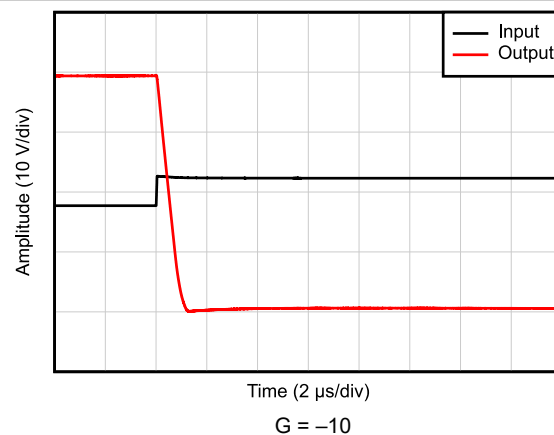


Figure 5-30. Negative Overload Recovery

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

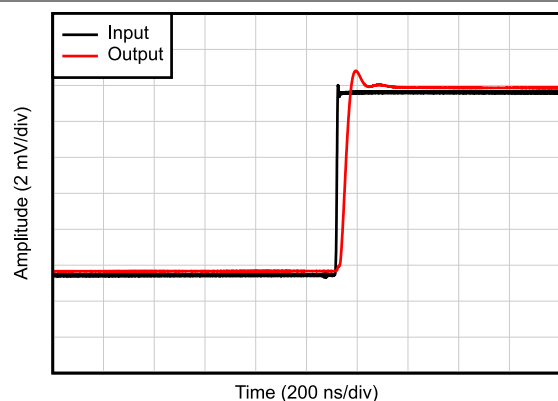


Figure 5-31. Small-Signal Step Response, Rising

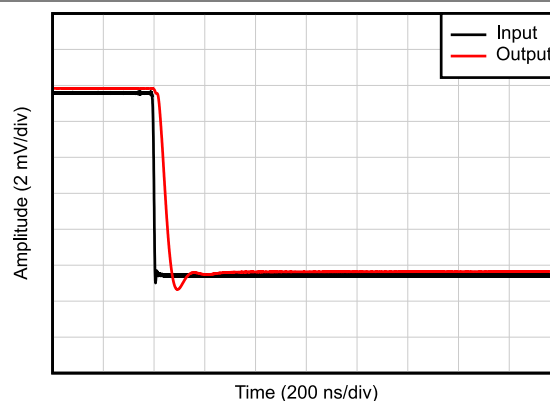


Figure 5-32. Small-Signal Step Response, Falling

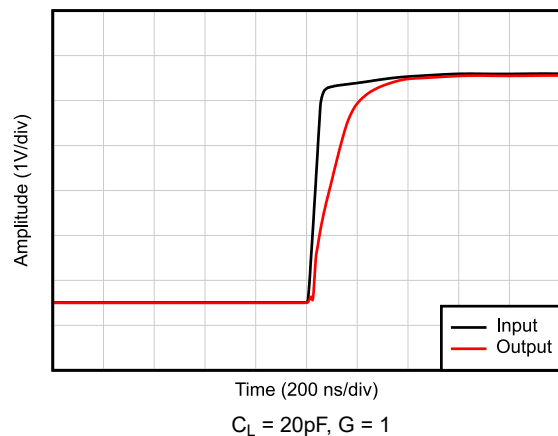


Figure 5-33. Large-Signal Step Response (Rising)

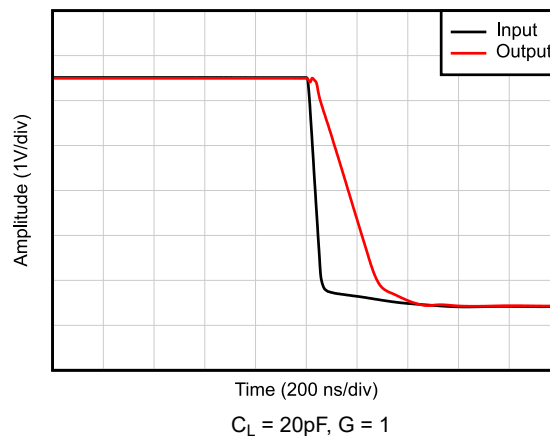


Figure 5-34. Large-Signal Step Response (Falling)

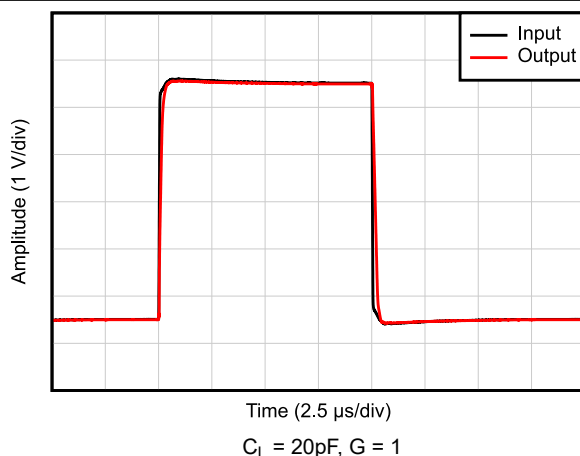


Figure 5-35. Large-Signal Step Response

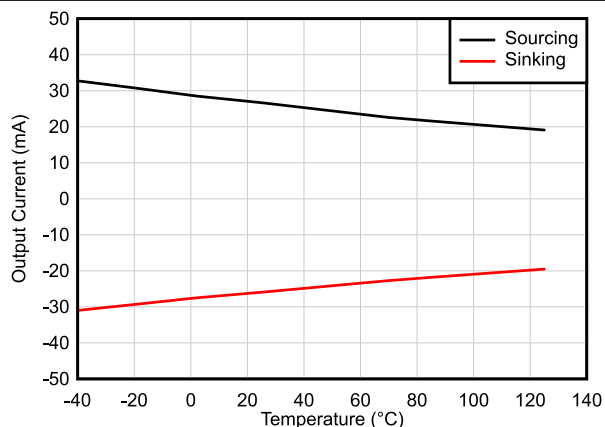


Figure 5-36. Short-Circuit Current vs Temperature

5.10 Typical Characteristics: TL08xH (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 40\text{V}$ ($\pm 20\text{V}$), $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{k}\Omega$ connected to $V_S / 2$, and $C_L = 20\text{pF}$ (unless otherwise noted)

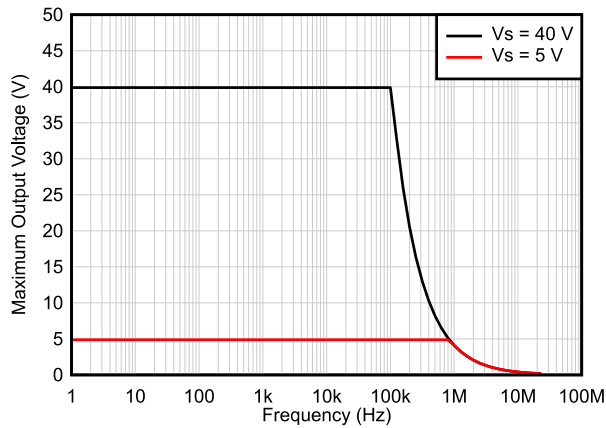


Figure 5-37. Maximum Output Voltage vs Frequency

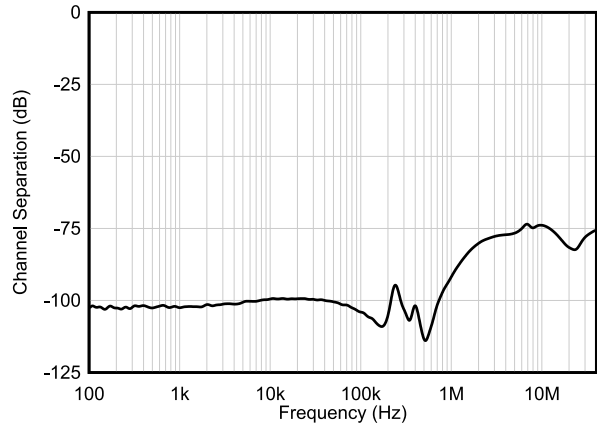


Figure 5-38. Channel Separation vs Frequency

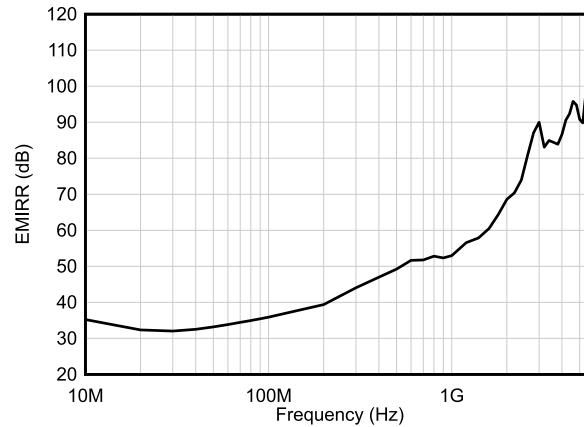


Figure 5-39. EMIRR (Electromagnetic Interference Rejection Ratio) vs Frequency

6 Parameter Measurement Information

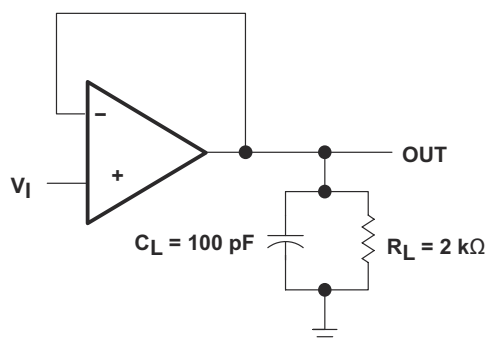


Figure 6-1. Test Figure 1

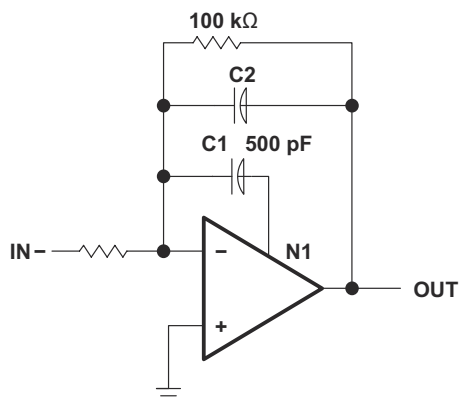


Figure 6-3. Test Figure 3

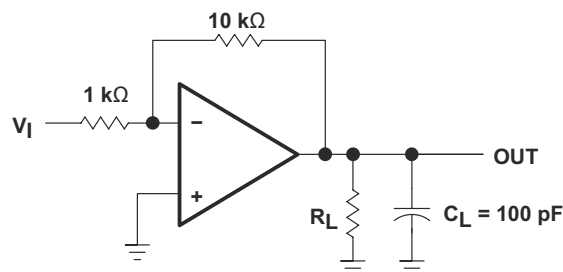


Figure 6-2. Test Figure 2

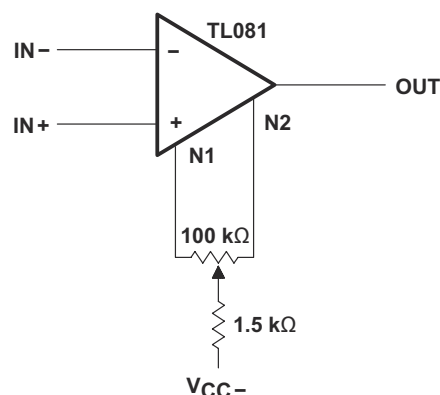


Figure 6-4. Test Figure 4

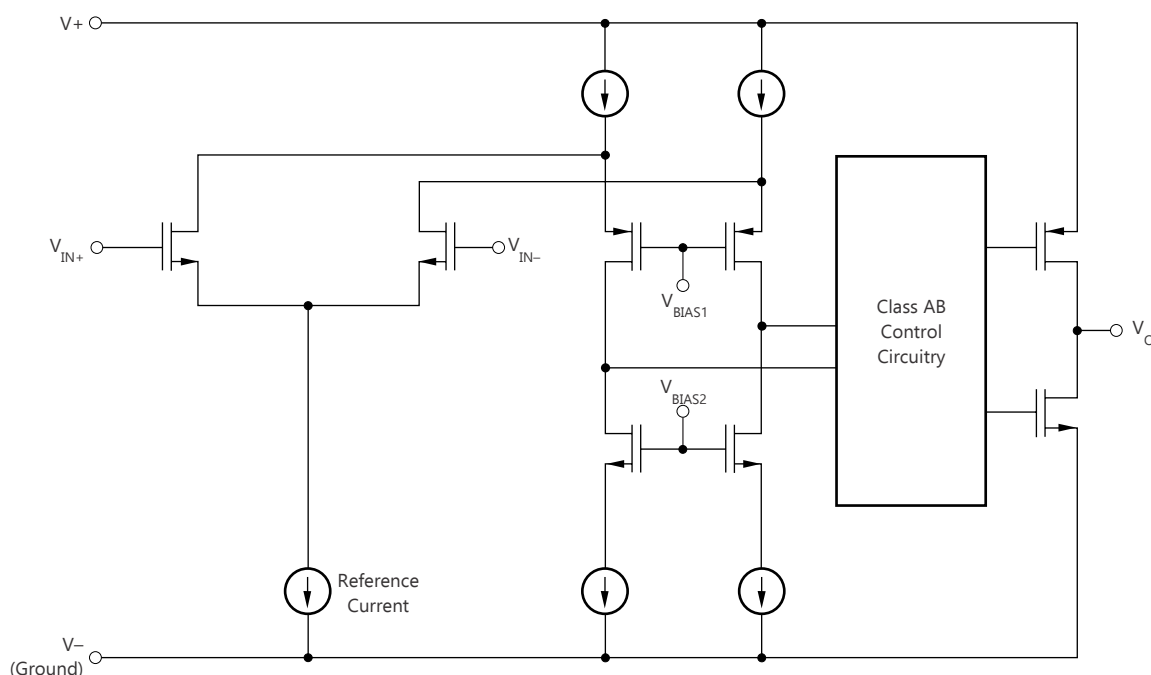
7 Detailed Description

7.1 Overview

The TL08xH family (TL081H, TL082H, and TL084H) is the next-generation family of the industry standard TL08x (TL081, TL082, and TL084) high-voltage general purpose amplifiers. These devices provide outstanding value for cost-sensitive applications requiring high slew rate with high voltage signals, such as motor drive and inverter systems.

A robust MUX-friendly input stage enhances flexibility in design, with common-mode voltage range extending to the positive rail as well as improved settling time in multi-channel applications. Low offset voltage (1mV, typ) and low offset voltage drift (2 μ V/°C) allows the TL08xH family to be used in rugged applications requiring precision current and voltage sensing. High voltage operation (up to 40V) and high slew rate (20V/ μ s) make the TL08xH family a premier choice for high-voltage applications with fast transients.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Total Harmonic Distortion

Harmonic distortions to an audio signal are created by electronic components in a circuit. Total harmonic distortion (THD) is a measure of harmonic distortions accumulated by a signal in an audio system. These devices have a very low THD of 0.003% meaning that the TL08x devices will add little harmonic distortion when used in audio signal applications.

7.3.2 Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. These devices have a 20V/ μ s slew rate.

7.4 Device Functional Modes

These devices are powered on when the supply is connected. This device can be operated as a single-supply operational amplifier or dual-supply amplifier depending on the application.

8 Applications and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TL08x series of operational amplifiers can be used in countless applications. The few applications in this section show principles used in all applications of these parts.

8.2 Typical Applications

8.2.1 Inverting Amplifier Application

A typical application for an operational amplifier in an inverting amplifier. This amplifier takes a positive voltage on the input, and makes it a negative voltage of the same magnitude. In the same manner, it also makes negative voltages positive.

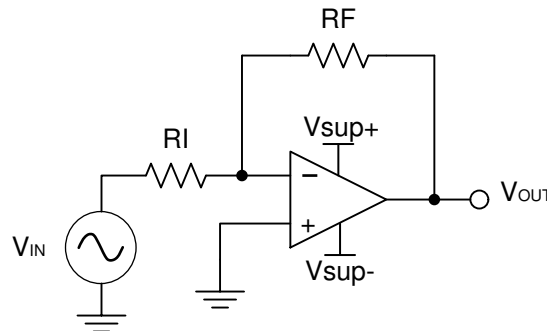


Figure 8-1. Schematic for Inverting Amplifier Application

8.2.1.1 Design Requirements

The supply voltage must be chosen such that it is larger than the input voltage range and output range. For instance, this application will scale a signal of $\pm 0.5\text{V}$ to $\pm 1.8\text{V}$. Setting the supply at $\pm 12\text{V}$ is sufficient to accommodate this application.

8.2.1.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier:

$$A_V = \frac{V_{OUT}}{V_{IN}} \quad (1)$$

$$A_V = \frac{1.8}{-0.5} = -3.6 \quad (2)$$

Once the desired gain is determined, choose a value for R_I or R_F . Choosing a value in the $\text{k}\Omega$ range is desirable because the amplifier circuit will use currents in the milliamp range. This causes the part will not draw too much current. This example will choose $10\text{k}\Omega$ for R_I which means $36\text{k}\Omega$ will be used for R_F . This was determined by Equation 3.

$$A_V = -\frac{R_F}{R_I} \quad (3)$$

8.2.1.3 Application Curve

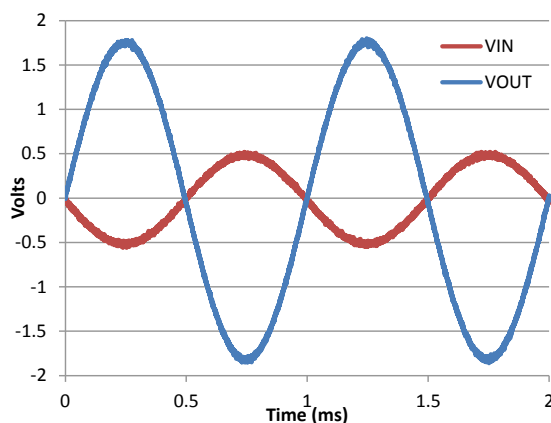


Figure 8-2. Input and Output Voltages of the Inverting Amplifier

8.3 System Examples

8.3.1 General Applications

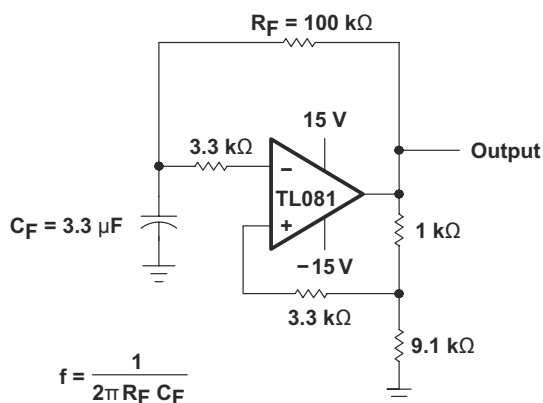


Figure 8-3. 0.5-Hz Square-Wave Oscillator

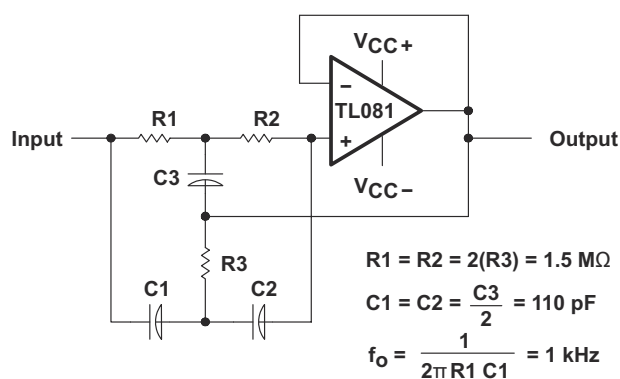


Figure 8-4. High-Q Notch Filter

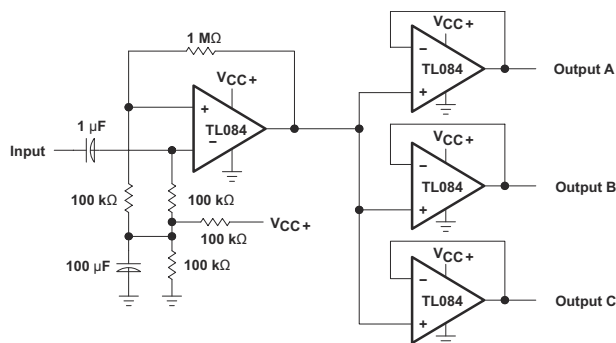
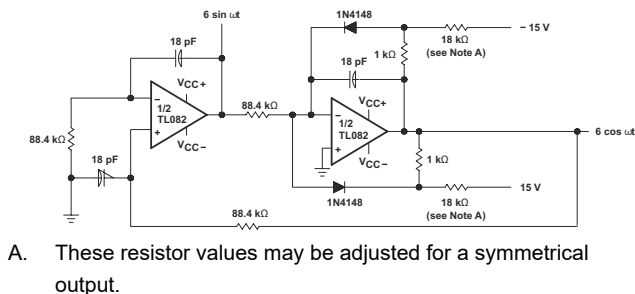


Figure 8-5. Audio-Distribution Amplifier



A. These resistor values may be adjusted for a symmetrical output.

Figure 8-6. 100-kHz Quadrature Oscillator

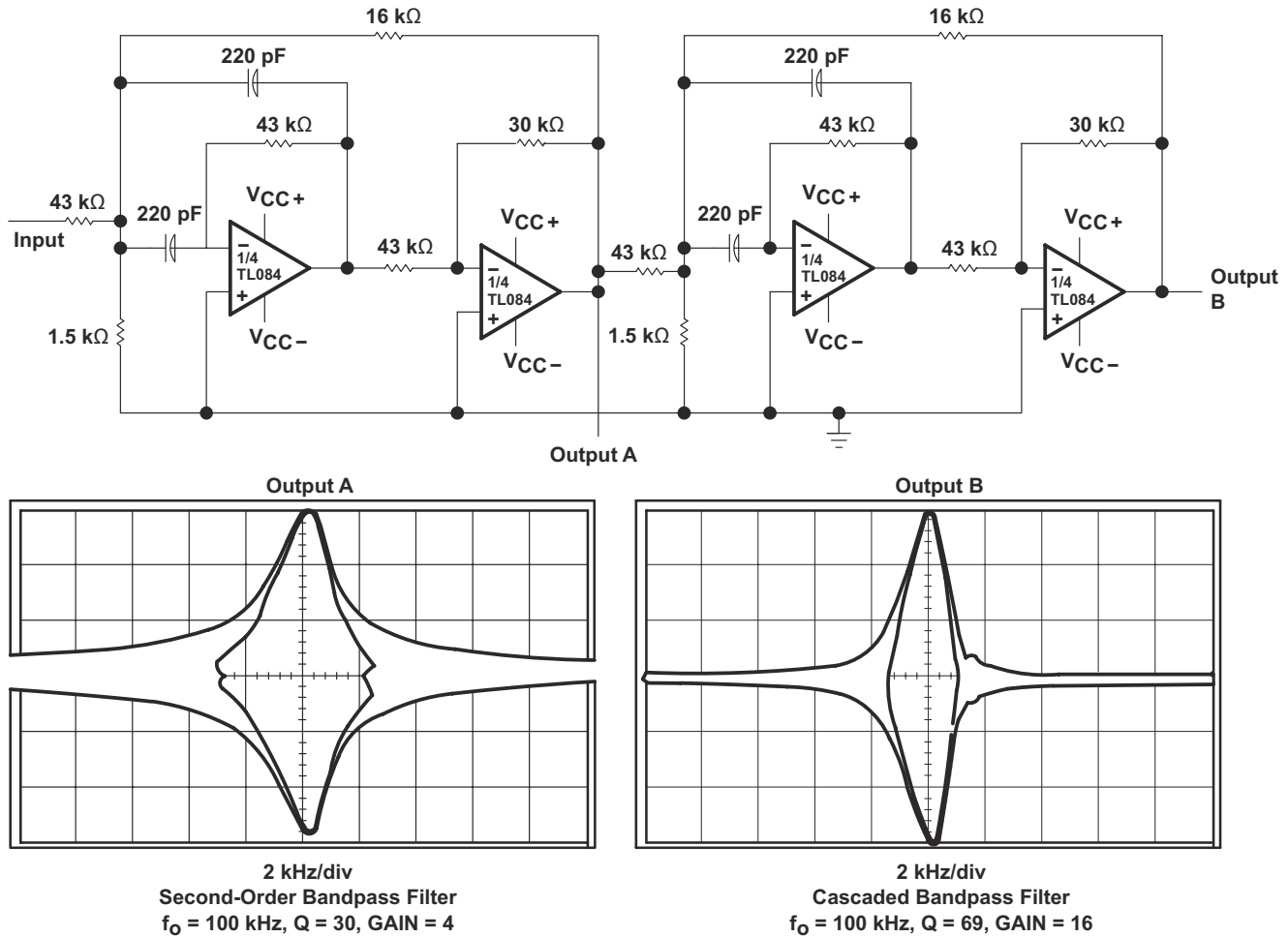


Figure 8-7. Positive-Feedback Bandpass Filter

8.4 Power Supply Recommendations

CAUTION

Supply voltages larger than 36V for a single-supply or outside the range of $\pm 18\text{V}$ for a dual-supply can permanently damage the device (see [Section 5.1](#)).

Place 0.1 μF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high impedance power supplies. For more detailed information on bypass capacitor placement, refer to [Section 8.5](#).

8.5 Layout

8.5.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1 μF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.

A ground plane helps distribute heat and reduces EMI noise pickup. Ensure to physically separate digital and analog grounds, paying attention to the flow of the ground current.

- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance, as shown in [Section 8.5.2](#).
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

8.5.2 Layout Examples

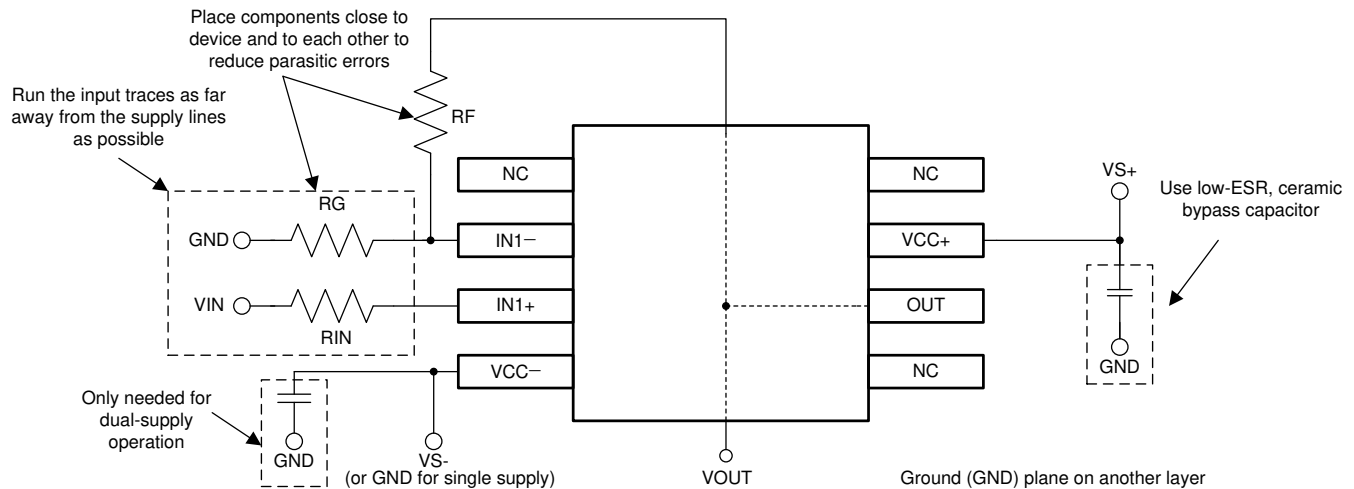


Figure 8-8. Operational Amplifier Board Layout for Noninverting Configuration

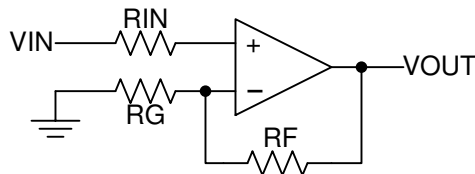


Figure 8-9. Operational Amplifier Schematic for Noninverting Configuration

9 Device and Documentation Support

9.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.2 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

9.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

9.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision M (December 2021) to Revision N (June 2024)	Page
• Changed Absolute Maximum Ratings, ESD Ratings, Recommended Operating Conditions, and Thermal Information sections by merging TL08xH and TL08xx specifications.....	9
• Changed Electrical Characteristics tables by merging TL08xC, TL08xAC, TL08xBC, TL08xI, and TL08xM specifications.....	14
• Increased gain bandwidth of all non-NS/non-PS packages and non-TL08xM devices from 3MHz to 5.25MHz.....	14
• Merged TL08xC, TL08xAC, TL08xBC, TL08xI, and TL08xM Switching Characteristics tables and renamed to Electrical Characteristics (AC).....	16
• Changed input voltage noise density at 1kHz for all non-PS/non-NS packages and all non-TL08xM devices to 37nV/√Hz.....	16
• Changed THD+N for all non-PS/non-NS packages and all non-TL08xM devices to 0.00012%.....	16
• Updated <i>Functional Block Diagram</i> and <i>Feature Description</i> sections.....	25

Changes from Revision L (July 2021) to Revision M (December 2021)	Page
• Corrected DCK pinout diagram and table in <i>Pin Configurations and Functions</i> section.....	3

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
5962-9851501Q2A	Active	Production	LCCC (FK) 20	55 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962- 9851501Q2A TL082MFKB
5962-9851501QPA	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9851501QPA TL082M
5962-9851503Q2A	Active	Production	LCCC (FK) 20	55 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962- 9851503Q2A TL084 MFKB
5962-9851503QCA	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9851503QC A TL084MJB
TL081ACD	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	0 to 70	081AC
TL081ACDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	081AC
TL081ACDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	081AC
TL081ACP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL081ACP
TL081ACP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL081ACP
TL081BCD	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	0 to 70	081BC
TL081BCDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	081BC
TL081BCDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	081BC
TL081BCP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL081BCP
TL081BCP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL081BCP
TL081CD	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	0 to 70	TL081C
TL081CDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL081C
TL081CDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL081C
TL081CP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL081CP
TL081CP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL081CP
TL081CPE4	Active	Production	PDIP (P) 8	50 TUBE	-	Call TI	Call TI	0 to 70	
TL081CPSR	Active	Production	SO (PS) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T081
TL081CPSR.A	Active	Production	SO (PS) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T081
TL081HIDBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	T81V

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TL081HIDBVR.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T81V
TL081HIDBVR.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T81V
TL081HIDCKR	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	1IP
TL081HIDCKR.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	1IP
TL081HIDR	Active	Production	SOIC (D) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL081D
TL081HIDR.A	Active	Production	SOIC (D) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL081D
TL081HIDR.B	Active	Production	SOIC (D) 8	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TL081ID	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	-40 to 85	TL081I
TL081IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL081I
TL081IDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL081I
TL081IP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	TL081IP
TL081IP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	TL081IP
TL082ACD	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	0 to 70	082AC
TL082ACDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC
TL082ACDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	082AC
TL082ACDRE4	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	0 to 70	
TL082ACP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL082ACP
TL082ACP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL082ACP
TL082ACPSR	Active	Production	SO (PS) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082A
TL082ACPSR.A	Active	Production	SO (PS) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082A
TL082BCD	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	0 to 70	082BC
TL082BCDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC
TL082BCDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC
TL082BCDRG4	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC
TL082BCDRG4.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	082BC
TL082BCP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL082BCP
TL082BCP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL082BCP
TL082BCPE4	Active	Production	PDIP (P) 8	50 TUBE	-	Call TI	Call TI	0 to 70	
TL082CDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C
TL082CDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL082C
TL082CDRE4	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	0 to 70	

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TL082CDRG4	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	0 to 70	
TL082CP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL082CP
TL082CP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL082CP
TL082CPSR	Active	Production	SO (PS) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082
TL082CPSR.A	Active	Production	SO (PS) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082
TL082CPSRG4	Active	Production	SO (PS) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082
TL082CPWR	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082
TL082CPWR.A	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T082
TL082CPWRG4	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	-	Call TI	Call TI	0 to 70	
TL082HIDDFR	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	082F
TL082HIDDFR.A	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	082F
TL082HIDDFR.B	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	082F
TL082HIDR	Active	Production	SOIC (D) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL082D
TL082HIDR.A	Active	Production	SOIC (D) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL082D
TL082HIPWR	Active	Production	TSSOP (PW) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	082HPW
TL082HIPWR.A	Active	Production	TSSOP (PW) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	082HPW
TL082IDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL082I
TL082IDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL082I
TL082IDRE4	Active	Production	SOIC (D) 8	2500 LARGE T&R	-	Call TI	Call TI	-40 to 85	
TL082IP	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	TL082IP
TL082IP.A	Active	Production	PDIP (P) 8	50 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	TL082IP
TL082IPE4	Active	Production	PDIP (P) 8	50 TUBE	-	Call TI	Call TI	-40 to 85	
TL082IPWR	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	Z082
TL082IPWR.A	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	Z082
TL082MFKB	Active	Production	LCCC (FK) 20	55 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962- 9851501Q2A TL082MFKB
TL082MFKB.A	Active	Production	LCCC (FK) 20	55 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962- 9851501Q2A TL082MFKB
TL082MJG	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	TL082MJG
TL082MJG.A	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	TL082MJG

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TL082MJGB	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9851501QPA TL082M
TL082MJGB.A	Active	Production	CDIP (JG) 8	50 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	9851501QPA TL082M
TL084ACDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084AC
TL084ACDR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084AC
TL084ACN	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL084ACN
TL084ACN.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL084ACN
TL084ACNSR	Active	Production	SOP (NS) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084A
TL084ACNSR.A	Active	Production	SOP (NS) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084A
TL084BCDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC
TL084BCDR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC
TL084BCDR.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	-	Call TI	Call TI	0 to 70	
TL084BCDR1G4	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC
TL084BCDR1G4.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084BC
TL084BCDRG4	Active	Production	SOIC (D) 14	2500 LARGE T&R	-	Call TI	Call TI	0 to 70	
TL084BCN	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL084BCN
TL084BCN.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL084BCN
TL084BCNE4	Active	Production	PDIP (N) 14	25 TUBE	-	Call TI	Call TI	0 to 70	
TL084CDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C
TL084CDR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084C
TL084CDRG4	Obsolete	Production	SOIC (D) 14	-	-	Call TI	Call TI	0 to 70	TL084C
TL084CN	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL084CN
TL084CN.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	0 to 70	TL084CN
TL084CNSR	Active	Production	SOP (NS) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084
TL084CNSR.A	Active	Production	SOP (NS) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	TL084
TL084CPWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T084
TL084CPWR.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T084
TL084CPWRG4	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	0 to 70	T084
TL084HIDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084HID
TL084HIDR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084HID

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TL084HIDYYR	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T084HDYY
TL084HIDYYR.A	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T084HDYY
TL084HIDYYR.B	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T084HDYY
TL084HIDYYRG4	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T084HDYY
TL084HIDYYRG4.A	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T084HDYY
TL084HIPWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	TL084PW
TL084HIPWR.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084PW
TL084ID	Obsolete	Production	SOIC (D) 14	-	-	Call TI	Call TI	-40 to 85	TL084I
TL084IDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I
TL084IDR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TL084I
TL084IDR.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	-	Call TI	Call TI	-40 to 125	
TL084IDR1G4	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084I
TL084IDR1G4.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084I
TL084IDRE4	Active	Production	SOIC (D) 14	2500 LARGE T&R	-	Call TI	Call TI	-40 to 85	
TL084IDRG4	Active	Production	SOIC (D) 14	2500 LARGE T&R	-	Call TI	Call TI	-40 to 85	
TL084IN	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	TL084IN
TL084IN.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	TL084IN
TL084ING4	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TL084IN
TL084ING4.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TL084IN
TL084MFK	Active	Production	LCCC (FK) 20	55 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	TL084MFK
TL084MFK.A	Active	Production	LCCC (FK) 20	55 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	TL084MFK
TL084MFKB	Active	Production	LCCC (FK) 20	55 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962- 9851503Q2A TL084 MFKB
TL084MFKB.A	Active	Production	LCCC (FK) 20	55 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962- 9851503Q2A TL084 MFKB

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TL084MJ	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	TL084MJ
TL084MJ.A	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	TL084MJ
TL084MJB	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9851503QC A TL084MJB
TL084MJB.A	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-9851503QC A TL084MJB
TL084QDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q
TL084QDR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q
TL084QDRG4	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q
TL084QDRG4.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TL084Q

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative

and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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OTHER QUALIFIED VERSIONS OF TL082, TL082M, TL084, TL084M :

- Catalog : [TL082](#), [TL084](#)
- Automotive : [TL082-Q1](#), [TL082-Q1](#)
- Military : [TL082M](#), [TL084M](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Military - QML certified for Military and Defense Applications